BCX56-10R1

Preferred Device

NPN Silicon Epitaxial Transistor

These NPN Silicon Epitaxial transistors are designed for use in audio amplifier applications. The device is housed in the SOT-89 package, which is designed for medium power surface mount applications.

- High Current: 1.0 Amp
- Available in 7 inch/1000 unit Tape and Reel
- Device Marking: BK

MAXIMUM RATINGS (T_C = 25° C unless otherwise noted)

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	VCEO	80	Vdc
Collector-Base Voltage	V _{CBO}	100	Vdc
Emitter-Base Voltage	V _{EBO}	5	Vdc
Collector Current	ιc	1	Adc
Total Power Dissipation @ T _A = 25°C Derate above 25°C	P _D (Note 1.) (Note 2.)	1.56 13 0.67 5.0	Watts mW/°C Watts mW/°C
Operating and Storage Temperature Range	TJ, T _{stg}	-65 to 150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Мах	Unit
Thermal Resistance Junction-to-Ambient (surface mounted)	R _θ JA (Note 1.) (Note 2.)	80 190	°C/W
Maximum Temperature for Soldering Purposes Time in Solder Bath	т	260 10	°C Sec

1. FR–4 @ 1.0 X 1.0 inch Pad

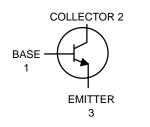
2. FR-4 @ Minimum Pad

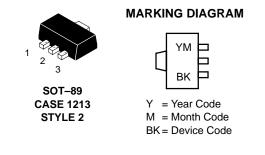


ON Semiconductor[™]

http://onsemi.com

MEDIUM POWER NPN SILICON HIGH CURRENT TRANSISTOR SURFACE MOUNT





ORDERING INFORMATION

Device	Package	Shipping
BCX56-10R1	SOT-89	1000/Tape & Reel

Preferred devices are recommended choices for future use and best overall value.

BCX56-10R1

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristics	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS			•	•	•
Collector-Base Breakdown Voltage $(I_C = 100 \ \mu Adc, I_E = 0)$	V(BR)CBO	100	-	-	Vdc
Collector-Emitter Breakdown Voltage $(I_C = 1.0 \text{ mAdc}, I_B = 0)$	V(BR)CEO	80	-	-	Vdc
Emitter-Base Breakdown Voltage (IE = 10 μ Adc, IC = 0)	V _{(BR)EBO}	5.0	-	-	Vdc
Collector-Base Cutoff Current ($V_{CB} = 30 Vdc, I_E = 0$)	ІСВО	-	-	100	nAdc
Emitter-Base Cutoff Current ($V_{EB} = 5.0 \text{ Vdc}, I_C = 0$)	IEBO	-	-	10	μAdc
ON CHARACTERISTICS (Note 3.)					
DC Current Gain $(I_C = 5.0 \text{ mA}, V_{CE} = 2.0 \text{ V})$ $(I_C = 150 \text{ mA}, V_{CE} = 2.0 \text{ V})$ $(I_C = 500 \text{ mA}, V_{CE} = 2.0 \text{ V})$	hfe	25 63 25		_ 160 _	_
Collector-Emitter Saturation Voltage $(I_C = 500 \text{ mAdc}, I_B = 50 \text{ mAdc})$	VCE(sat)	-	-	0.5	Vdc
Base-Emitter On Voltage (I _C = 500 mAdc, V _{CE} = 2.0 Vdc)	V _{BE(on)}	-	-	1.0	Vdc
DYNAMIC CHARACTERISTICS					
Current-Gain – Bandwidth Product (I _C = 10 mAdc, V_{CE} = 5.0 Vdc, f = 35 MHz)	fT	-	130	-	MHz

3. Pulse Test: Pulse Width $\leq 300~\mu s,~\text{Duty}~\text{Cycle} \leq 2.0\%$

TYPICAL ELECTRICAL CHARACTERISTICS

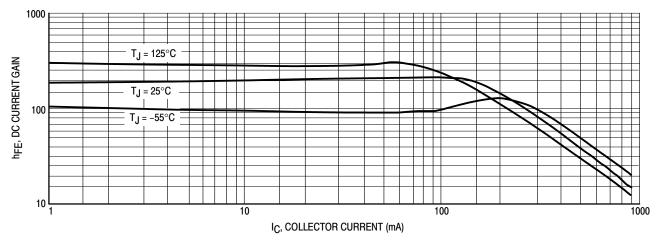
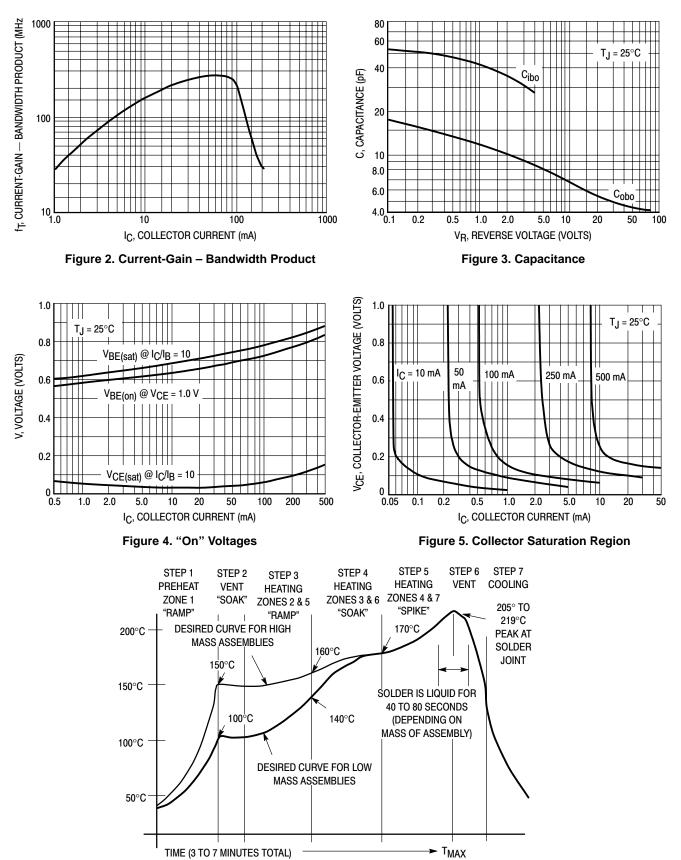


Figure 1. DC Current Gain

BCX56-10R1

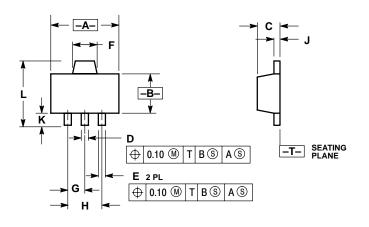


TYPICAL ELECTRICAL CHARACTERISTICS



PACKAGE DIMENSIONS





	1, 1982.				
CONTROLLING DIMENSION: MILLIMETERS					
213-0	213-01 OBSOLETE, NEW STANDARD 121				
	MILLIN	IETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	4.40	4.60	0.173	0.181	
В	2.40	2.60	0.094	0.102	
С	1.40	1.60	0.055	0.063	
D	0.37	0.57	0.015	0.022	
Е	0.32	0.52	0.013	0.020	
F	1.50	1.83	0.059	0.072	
G	H 3.00 BSC 0.118 BSC		BSC		
Н			0.118	BSC	
J			0.012	0.020	
K	0.80		0.031		
Г		4.25		0.167	

1. DIMENSIONING AND TOLERANCING PER ANSI

STYLE 2:

NOTES

PIN 1. BASE 2. COLLECTOR 3. EMITTER

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